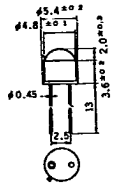
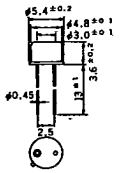
SILICON PIN PHOTODIODES

MI-11HL

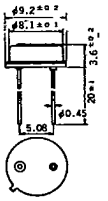


MI-11H

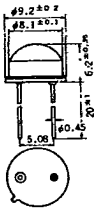


Ta=25°C

MI-33H



MI-33HL



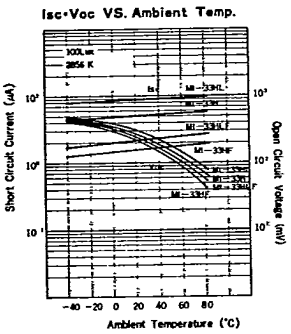
unit : mm

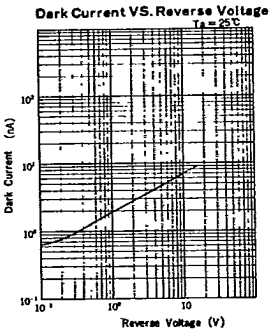
Maximum Ratings

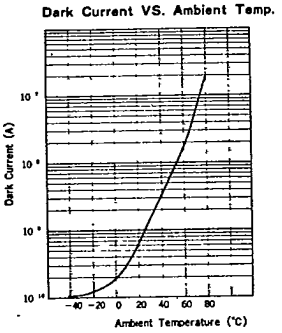
Ratings	Symbol	MI-11H	MI-11HL	MI-33H	MI-33HL	Units
Reverse Voltage	V_R	30	30	32	32	V
Power Dissipation	P	25	25	200	200	mW
Operating Temperature	Topr.	−20 ~ +80		−20 ~ +80		°C
Storage Temperature	Tstg.	−20 ~ +80		−20 ~ +80		°C

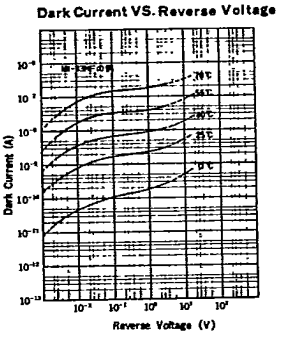
Characteristics

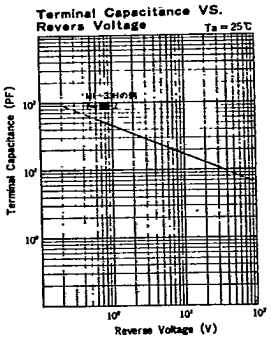
Ratings	Symbol	Conditions	MI-11H MIN. TYP. MAX.	MI-11HL MIN. TYP. MAX.	MI-33H MIN. TYP. MAX.	MI-33HL MIN. TYP. MAX.	Units
Short Circuit Current	Ish	2856K 1000Lux	5 8	20 50	40 55 70	80 110 140	μA
Dark Current	Id	V_R= 10V R_H< 65%	1	1	5 50	5 50	nA
Peak Sensitivity Wavelength	λp		950	950	950	950	nm
Terminal Capacitance	Ct	V_R= 10V f= 1 MHz	4	4	15 20 25	15 20 25	pF
Response Time	tr. tf	V_R= 15V R_L= 1 kΩ	0.05	0.05	0.3	0.3	μs

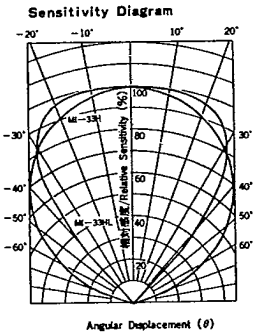




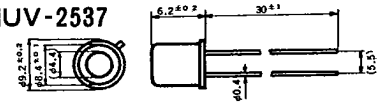






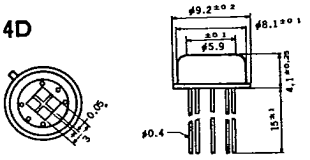


MUV-2537



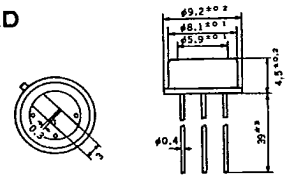
(Isc) 6×10^{-8}A (TYP) at 300μW/cm²
(Voc) 900mV (TYP) at 300μW/cm²
(Id) 1×10^{-11}A (MAX) at V_R= 1 V
(λp) 250nm

MI-33H-4D



(Isc) 1 14 μA (TYP.) at1000Lux
(Id) 1 0.1 nA (TYP.) at V_R=1 V
(Ct) 1 7 pF (TYP.) f=1MHz, V_R=10V
(λp) 930 nm

MI-33H-2D



(Isc) 1 30μA (TYP.) at 1000Lux
(Id) 1 10nA (TYP.) at V_R= 1 V
15% (MAX.)
(λp) 930nm

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